

# 1N4153

## FEATURES :

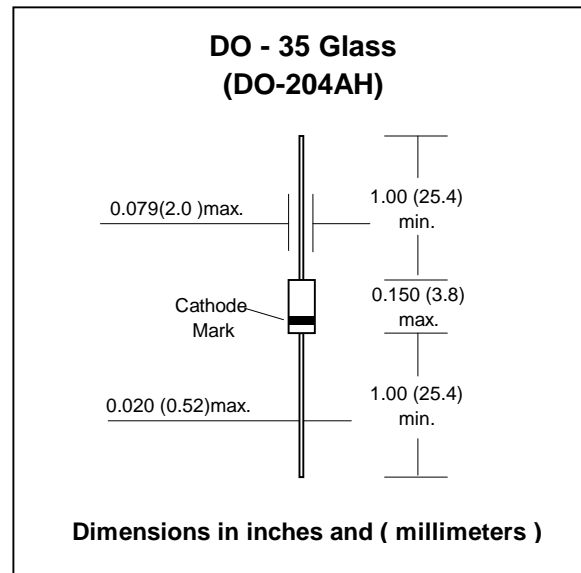
- High switching speed: max. 2 ns
- Peak reverse voltage: max. 75 V
- Pb / RoHS Free

## MECHANICAL DATA :

**Case:** DO-35 Glass Case

**Weight:** approx. 0.13g

## HIGH SPEED SWITCHING DIODE



## Maximum Ratings and Thermal Characteristics (Rating at 25 °C ambient temperature unless otherwise specified.)

Parameter	Symbol	Value	Unit
Maximum Peak Reverse Voltage	$V_{RM}$	75	V
Maximum Continuous Forward Current	$I_F$	300	mA
Maximum Average Forward Current	$I_{F(AV)}$	150	mA
Maximum Peak Forward Current at t = 1s	$I_{FSM}$	0.25	A
Maximum Power Dissipation	$P_D$	500	mW
Maximum Junction Temperature	$T_J$	175	°C
Storage Temperature Range	$T_S$	-65 to + 200	°C

## Electrical Characteristics ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse Current	$I_R$	$V_R = 50\text{ V}$	-	-	0.05	$\mu\text{A}$
		$V_R = 50\text{ V}, T_J = 150\text{ }^\circ\text{C}$	-	-	50	$\mu\text{A}$
Forward Voltage	$V_F$	$I_F = 20\text{ mA}$	-	-	0.88	V
Reverse Breakdown Voltage	$V_{(BR)R}$	$I_R = 5\text{ A (pulsed)}$	75	-	-	V
Diode Capacitance	$C_d$	$f = 1\text{ MHz}; V_R = 0$	-	-	2.0	pF
Reverse Recovery Time	$T_{rr1}$	$I_F = 10\text{ mA to } I_R = 10\text{ mA}$ to $I_R = 1\text{ mA}$	-	-	4	ns
	$T_{rr2}$	$I_F = 10\text{ mA to } V_R = 6\text{ V}$ $R_L = 100\Omega, I_R = 1\text{ mA}$	-	-	2	ns